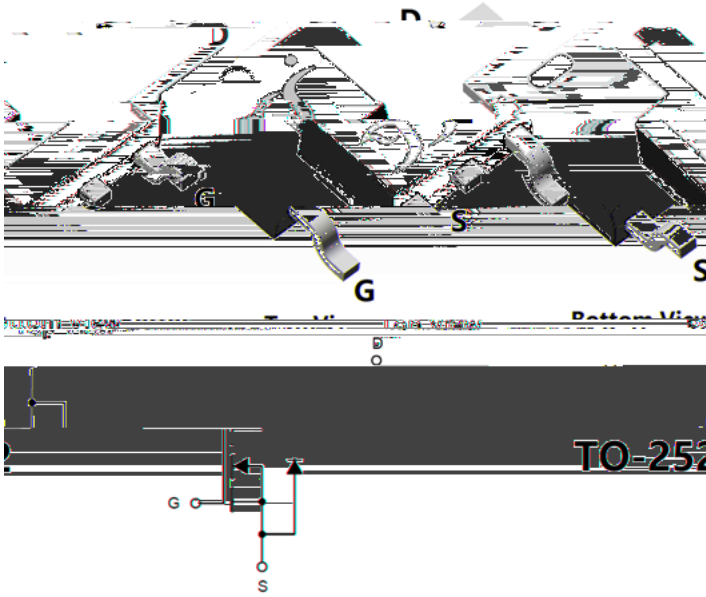




N-Channel Enhancement Mode Field Effect Transistor

Product Summary

- V_{DS} 40V
- I_D 100A
- $R_{DS(ON)}$ (at $V_{GS}=10V$)



Parameter			Symbol	Limit	Unit
Drain-source Voltage			V_{DS}	40	V
Gate-source Voltage			V_{GS}	± 20	V
Continuous Drain Current (Note 1,2)	Steady-State	$T_A=25$	I_D	19	A
		$T_A=100$		13	
Continuous Drain Current (Note 1,3)	Steady-State	$T_C=25$		100	
		$T_C=100$		70	
Pulsed Drain Current	$T_C=25$, $t_p=100\mu s$		I_{DM}	400	A
Avalanche energy	$V_G=10V$, $R_G=25\Omega$, $L=0.5mH$, $I_{AS}=25.4A$		EAS	161.29	mJ
Total Power Dissipation (Note 1,2)	Steady-State	$T_A=25$	P_D	2.7	W
		$T_A=100$		1.3	

Total Power Dissipation
(Note 1,3)

Steady-State Max

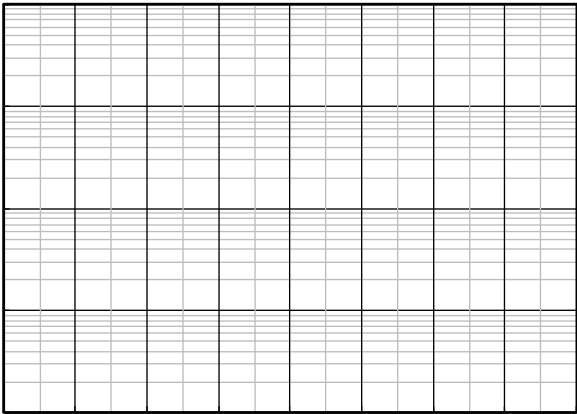
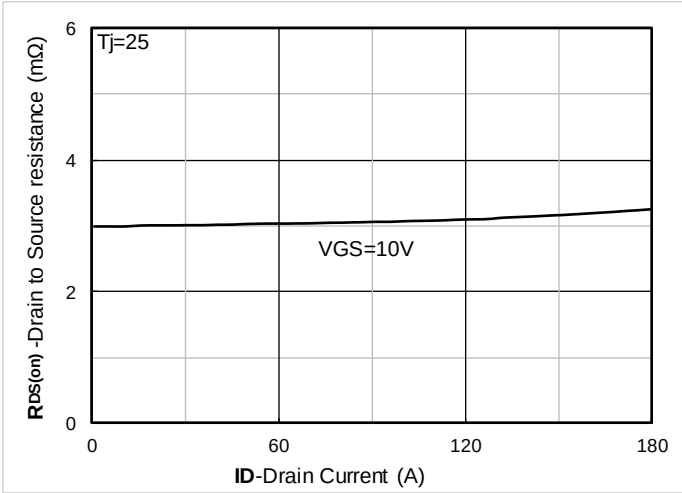
					Units
Thermal Resistance Junction-to-Ambient (Note 2)	Steady-State	$R_{\theta JA}$	45	55	/W
Thermal Resistance Junction-to-Case	Steady-State	$R_{\theta JC}$	1.5	1.8	

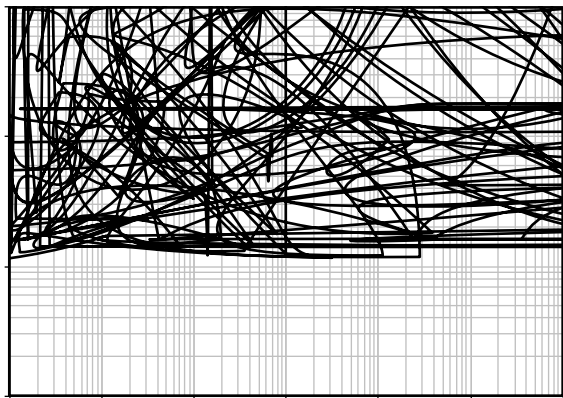
■ Ordering Information (Example)

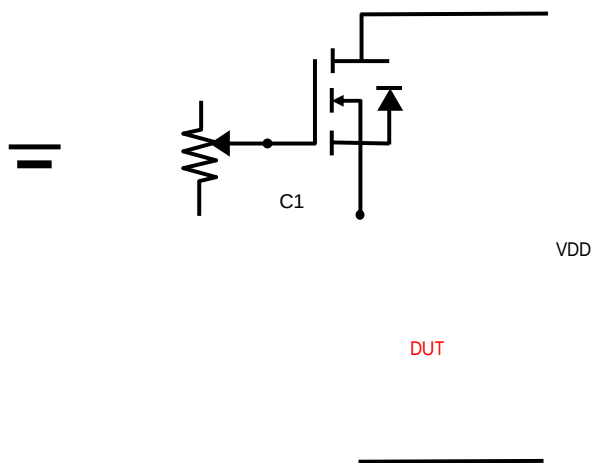
PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJD3D8G04HHQ	F1/F2	YJD3D8G04H	2500	/	25000	13"Reel



y









■ TO-252-B Package information

SYMBOL	b	MIN.
		0.000
A2		
b		0.030
c		
D		
D2		
E		
E1		

< - ' ' * ++4

<DQJJKRX <DQJMLH (OHFWURQL